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(71) Applicant (*for all designated States except US*): IMPERIAL COLLEGE INNOVATIONS LIMITED [GB/GB]; Level 12, Electrical Engineering Building, Imperial College London, Exhibition Road, London SW7 2BT (GB).

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(72) Inventor; and

(75) Inventor/Applicant (*for US only*): GREEN, Mino [GB/GB]; 55 Gerard Road, Barnes, London SW13 9QH (GB).

(54) Title: STRUCTURED SILICON ANODE

(57) Abstract: A silicon/lithium battery which can be fabricated from a silicon substrate allowing it to be produced as an integrated unit on a chip, the battery comprising a silicon anode formed from sub-micron diameter pillars of silicon fabricated on an n-type silicon wafer.

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